

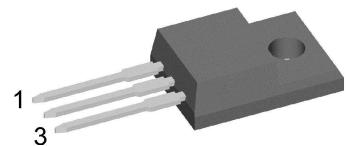
Schottky Diode Gen 2

V_{RRM} = 60 V
 I_{FAV} = 2x 10 A
 V_F = 0.62 V

High Performance Schottky Diode
 Low Loss and Soft Recovery
 Common Cathode

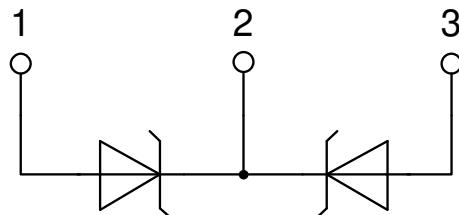
Part number

DSB20C60PN



Backside: isolated

 E72873



Features / Advantages:

- Very low V_F
- Extremely low switching losses
- Low I_{rm} values
- Improved thermal behaviour
- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching

Applications:

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

Package: TO-220FP

- Isolation Voltage: 2500 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Soldering pins for PCB mounting
- Base plate: Plastic overmolded tab
- Reduced weight

Disclaimer Notice

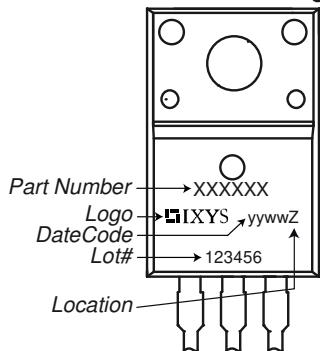
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Schottky

Symbol	Definition	Conditions	Ratings			
			min.	typ.	max.	
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^\circ C$			60	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^\circ C$			60	V
I_R	reverse current, drain current	$V_R = 60 V$ $V_R = 60 V$	$T_{VJ} = 25^\circ C$ $T_{VJ} = 100^\circ C$		4 35	mA
V_F	forward voltage drop	$I_F = 10 A$ $I_F = 20 A$ $I_F = 10 A$ $I_F = 20 A$	$T_{VJ} = 25^\circ C$ $T_{VJ} = 125^\circ C$		0.69 0.93 0.62 0.82	V
I_{FAV}	average forward current	$T_C = 110^\circ C$ rectangular $d = 0.5$	$T_{VJ} = 150^\circ C$		10	A
V_{F0} r_F	threshold voltage slope resistance } for power loss calculation only		$T_{VJ} = 150^\circ C$		0.44 16.1	V mΩ
R_{thJC}	thermal resistance junction to case				4.5	K/W
R_{thCH}	thermal resistance case to heatsink				0.5	K/W
P_{tot}	total power dissipation		$T_C = 25^\circ C$		30	W
I_{FSM}	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}; V_R = 0 V$	$T_{VJ} = 45^\circ C$		240	A
C_J	junction capacitance	$V_R = 12 V$ f = 1 MHz	$T_{VJ} = 25^\circ C$		149	pF

Package TO-220FP

Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			35	A
T_{VJ}	virtual junction temperature		-55		150	°C
T_{op}	operation temperature		-55		125	°C
T_{stg}	storage temperature		-55		150	°C
Weight				2		g
M_d	mounting torque		0.4		0.6	Nm
F_c	mounting force with clip		20		60	N
$d_{Spp/App}$	creepage distance on surface / striking distance through air	terminal to terminal	1.6	1.0		mm
$d_{Spb/Abp}$		terminal to backside	2.5	2.5		mm
V_{ISOL}	isolation voltage	t = 1 second t = 1 minute 50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA	2500 2100			V V

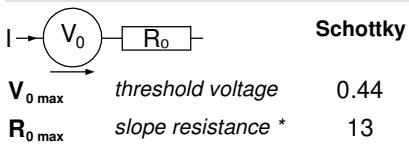
Product Marking

Part description

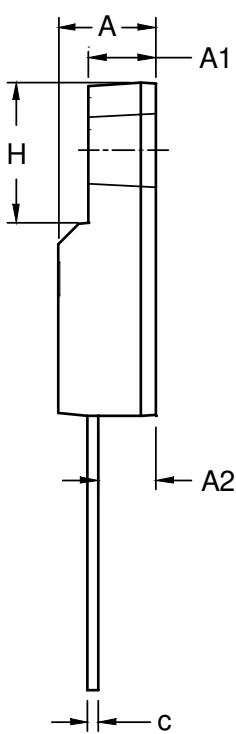
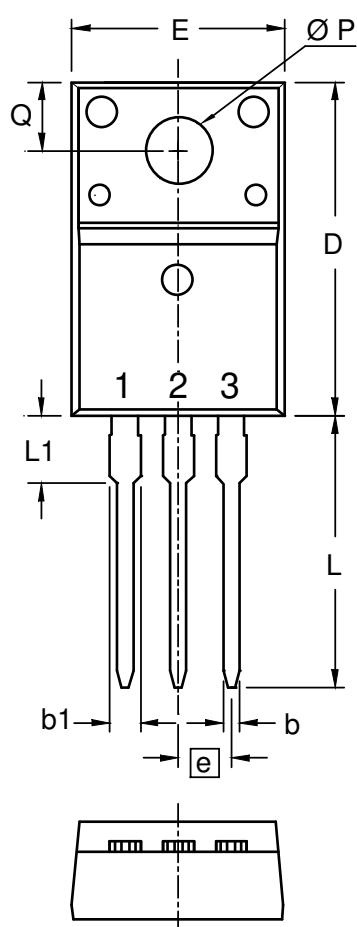
D = Diode
S = Schottky Diode
B = ultra low VF
20 = Current Rating [A]
C = Common Cathode
60 = Reverse Voltage [V]
PN = TO-220ABFP (3)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSB20C60PN	DSB20C60PN	Tube	50	508864

Equivalent Circuits for Simulation

* on die level

 $T_{VJ} = 150^\circ\text{C}$ 

Outlines TO-220FP


Dim.	Millimeters		Inches	
	min	max	min	max
A	4.50	4.90	0.177	0.193
A1	2.34	2.74	0.092	0.108
A2	2.56	2.96	0.101	0.117
b	0.70	0.90	0.028	0.035
c	0.45	0.60	0.018	0.024
D	15.67	16.07	0.617	0.633
E	9.96	10.36	0.392	0.408
e	2.54 BSC		0.100 BSC	
H	6.48	6.88	0.255	0.271
L	12.68	13.28	0.499	0.523
L1	3.03	3.43	0.119	0.135
ØP	3.08	3.28	0.121	0.129
Q	3.20	3.40	0.126	0.134

